UNISONIC TECHNOLOGIES CO., LTD

MGBR40V150C DIODE

DUAL MOS GATED BARRIER RECTIFIER

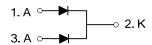
■ DESCRIPTION

The UTC **MGBR40V150C** is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

■ FEATURES

- * Very low forward voltage drop
- * High switching speed

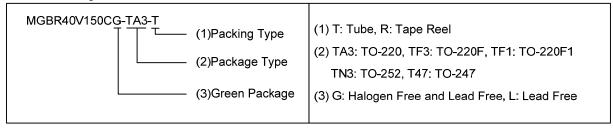
■ SYMBOL



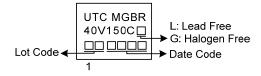
■ ORDERING INFORMATION

Ordering Number		Dooleage	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR40V150CL-TA3-T	MGBR40V150CG-TA3-T	TO-220	Α	K	Α	Tube	
MGBR40V150CL-TF1-T	MGBR40V150CG-TF1-T	TO-220F1	Α	K	Α	Tube	
MGBR40V150CL-TF3-T	MGBR40V150CG-TF3-T	TO-220F	Α	K	Α	Tube	
MGBR40V150CL-TN3-R	R40V150CL-TN3-R MGBR40V150CG-TN3-R		Α	K	Α	Tape Reel	
MGBR40V150CL-T47-T	MGBR40V150CG-T47-T	TO-247	Α	K	Α	Tube	

Note: Pin Assignment: A: Anode K: Cathode



■ MARKING



TO-220F

TO-220F

TO-252

TO-252

TO-247

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■ ABSOLUTE MAXIMUM RATINGS (PER LEG) (T_A=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage		V_{RM}	150	V
Working Peak Reverse Voltage		V_{RWM}	150	V
Peak Repetitive Reverse Voltage		V_{RRM}	150	V
Average Rectified Output Current Per Device	Per Leg	Io	20	Α
	Total		40	Α
Non-Repetitive Peak Forward Surge Current 8 Half Sine-Wave Superimposed on Rated Load	•	I _{FSM}	250	А
Operating Junction Temperature		TJ	-65 ~ + 150	°C
Storage Temperature		T_{STG}	-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Typical Thermal Resistance	TO-220		2	°C/W	
	TO-220F TO-220F1	θυς	4	°C/W	
	TO-247		1.5	°C/W	
	TO-252		2.8	°C/W	

■ ELECTRICAL CHARACTERISTICS (PER LEG) (T_A =25°C unless otherwise specified.)

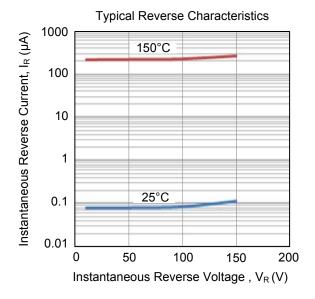
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I _R =0.50mA	150			V
Forward Voltage Drop	V _{FM}	I _F =5A, T _J =25°C		0.67		V
		I _F =5A, T _J =125°C		0.53		V
		I _F =10A, T _J =25°C		0.72		V
		I _F =10A, T _J =125°C		0.59		V
		I _F =20A, T _J =25°C		0.79	0.85	V
		I _F =20A, T _J =125°C		0.67	0.78	V
Leakage Current (Note 1)	DM	V _R =150V, T _J =25°C			100	μA
		V _R =150V, T _J =125°C			10	mA

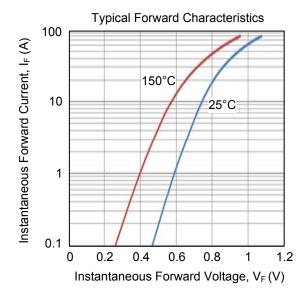
Notes: 1. Short duration pulse test used to minimize self-heating effect.

^{2.} Thermal resistance junction to case mounted on heatsink.

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■ TYPICAL CHARACTERISTICS





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